

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:  
Hwang, et al.

Serial No.: 10/092,456

Confirmation No.: 1212

Filed: March 6, 2002

For: Etching Methods for a Magnetic  
Memory Cell Stack

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

§ Group Art Unit: 2818

§ Examiner: D. A. Le

#7/Election  
w/ A  
margin  
11/21/02

CERTIFICATE OF MAILING 37 CFR 1.8	
I hereby certify that this correspondence is being deposited on November 5, 2002, with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.	
Nov, 5, 2002	<i>Ari Hammer</i>
Date	Signature

## RESPONSE TO RESTRICTION REQUIREMENT DATED OCTOBER 15, 2002

In response to the Restriction Requirement dated October 15, 2002, having a shortened statutory period for response set to expire on November 15, 2002, please enter this response and reconsider the claims pending in the application for reasons discussed below. Although Applicants believe that no fee is due in connection with this response, the Commissioner is hereby authorized to charge counsel's Deposit Account No. 20-0782/AMAT/6437/ETCH/METAL/BTP for any fees, including extension of time fees or excess claim fees, required to make this response timely and acceptable to the Office.

**IN THE CLAIMS:**

1. (Cancelled) A method for forming a magnetic memory cell, comprising:  
loading a semiconductor wafer into an etch process chamber, the semiconductor wafer having at least one masking layer, the at least one masking layer formed over a set of layers for forming the magnetic memory cell, the set of layers including a subset